

GS5A - GS5M SURFACE MOUNT SILICON RECTIFIER DIODES

VOLTAGE RANGE: 50 - 1000V CURRENT: 5.0 A

Features

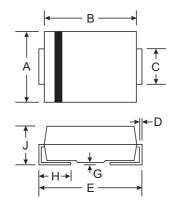
- Glass Passivated Die Construction
- Ideally Suited for Automatic Assembly
- Low Forward Voltage Drop
- Low Power Loss
- Built-in Strain Relief
- Plastic Case Material has UL Flammability Classification Rating 94V-O

Mechanical Data

- Case: SMC/DO-214AB, Molded Plastic
- Terminals: Solder Plated, Solderable per MIL-STD-750, Method 2026
- Polarity: Cathode Band or Cathode Notch
- Marking: Type Number
- Weight: 0.21 grams (approx.)







SMC/DO-214AB						
Dim	Min	Max				
Α	5.59	6.22				
В	6.60	7.11				
С	2.75	3.18				
D	0.15	0.31				
E	7.75	8.13				
G	0.10	0.20				
Н	0.76	1.52				
J	2.00	2.62				
All Dimensions in mm						

Maximum Ratings and Electrical Characteristics T_A = 25°C unless otherwise specified

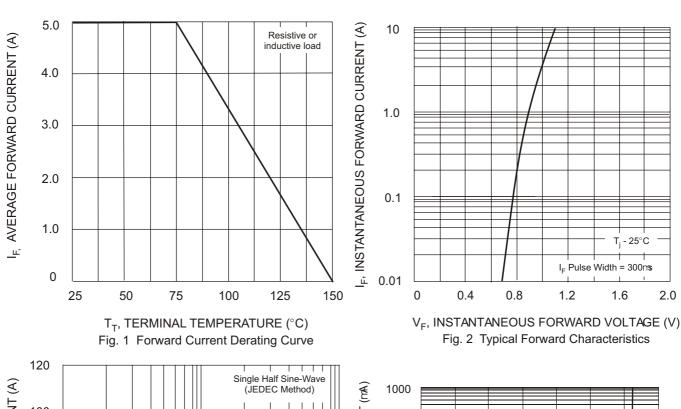
Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

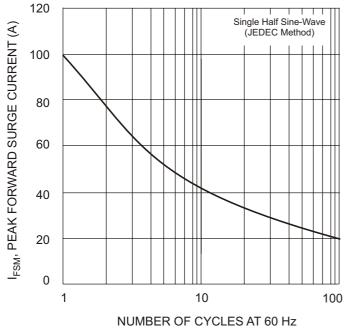
Characteristic	Symbol	GS5A	GS5B	GS5D	GS5G	GS5J	GS5K	GS5M	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	VRRM VRWM VR	50	100	200	400	600	800	1000	V
RMS Reverse Voltage	VR(RMS)	35	70	140	280	420	560	700	V
Average Rectified Output Current @T _L = 75°C	lo	5.0						Α	
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	IFSM				100				А
Forward Voltage @I _F = 5.0A	VFM	1.15						V	
	IRM	10 250						μA	
Typical Junction Capacitance (Note 1)	Cj				40				pF
Typical Thermal Resistance (Note 2)	R ⊕ JL				10				°C/W
Operating and Storage Temperature Range	Tj, Tstg			-	65 to +15	50			°C

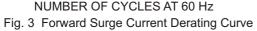
Note: 1. Measured at 1.0 MHz and applied reverse voltage of 4.0 V DC.

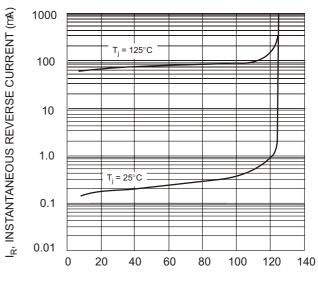
2. Mounted on P.C. Board with 8.0mm² land area.











PERCENT OF RATED PEAK REVERSE VOLTAGE (%) Fig. 4 Typical Reverse Characteristics